

A hybrid integrated external cavity laser for atomic quantum technologies

MATTHEW DAY, NIKOLAY VIDENOV, RAJIBUL ISLAM, DAVID CORY

Motivation and design

• Optical systems are a critical limiting factor in atomic quantum technologies • Photonic integrated circuits offer a solution by reducing lab-sized optical systems to the chip-scale • As a first step, we fabricate an external laser cavity in an aluminum nitride waveguide circuit and use it to demonstrate single-mode lasing of a diode

Figure 1 Principle of integrated external cavity diode laser. A laser diode is coupled into a waveguide. Two rings of slightly different dimension form a Vernier filter for selecting a single frequency mode of the diode gain spectrum, which is reflected back to the diode. Electrodes can tune the phase and wavelength of the cavity.



Fabrication

Figure 2 (Top L) AlN waveguide on sapphire, (Top R) False colour cross-section of AIN edge coupler, (Bottom L) External cavity in AIN waveguide circuit, (Bottom R) Array of 42 laser cavities on a single chip mid-fabrication.



• AIN on sapphire waveguides are fabricated by first patterning a resist using electron beam lithography • The resist is transferred into the AIN film using reactive ion etching Waveguides are clad in low-index silicon nitride to reduce losses and form a surface for electrode patterning

• Electrodes are patterned using UV lithography and metal lift-off

• Waveguide facets are exposed by dicing and polishing

Results

Single-mode lasing

resolution

Figure 3 Observation of single-mode lasing in AlN photonic chip. (Top) Laser light circulating in both filter rings, (Bottom L) Resolution-limited lasing spectrum, (Bottom R) Measurement setup with diode, chip and fiber array.



2500

2000

<u> კ</u> 1500-1000

• A gain chip with 655 nm central wavelength is edge-coupled into an AIN waveguide chip

• Feedback is observed with light circulating in both rings simultaneously • A single-frequency spectrum is measured at 655.954 nm, narrowing the laser linewidth below the spectrometer







Figure 4 Preliminary demonstration of electro-optic tuning in a racetrack resonator. (Left) False colour image of electrodes (beige) over AIN waveguides (purple) on SiNx cladding (blue), (Right) Racetrack transmission spectrum for increasing applied voltage.



• Elecro-optic tuning of a racetrack resonator has been observed at 852 nm • The resonance of the racetrack can be linearly shifted by 35 MHz/V • Further work is required to increase the electro-optic response, test at visible wavelengths and integrate with a laser cavity

Acknowledgments: This research was undertaken thanks in part to funding from the Canada First Research Excellence Fund, [list others] as appropriate].



Electro-optic tuning